

Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit

Silicon PIN Photodiode with Very Short Switching Time

SFH 229

SFH 229 FA



SFH 229



SFH 229 FA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 380 nm bis 1100 nm (SFH 229) und bei 880 nm (SFH 229 FA)
- Kurze Schaltzeit (typ. 10 ns)
- 3 mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

Anwendungen

- Lichtschranken für Gleich- und Wechselbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 380 nm to 1100 nm (SFH 229) and of 880 nm (SFH 229 FA)
- Short switching time (typ. 10 ns)
- 3 mm LED plastic package
- Also available on tape and reel

Applications

- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
SFH 229	Q62702-P215
SFH 229 FA	Q62702-P216

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ($t \leq 3$ s)	T_S	230	°C
Sperrspannung Reverse voltage	V_R	20	V
Verlustleistung Total power dissipation	P_{tot}	150	mW

Kennwerte ($T_A = 25$ °C)

Characteristics

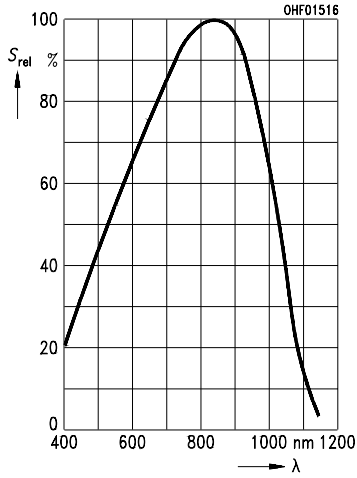
Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 229	SFH 229 FA	
Fotostrom Photocurrent $V_R = 5$ V, Normlicht/standard light A, $T = 2856$ K, $E_V = 1000$ lx $V_R = 5$ V, $\lambda = 950$ nm, $E_e = 1$ mW/cm ²	I_P	28 (≥ 18)	–	μ A
	I_P	–	20 (≥ 10.8)	μ A
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	860	900	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	380 ... 1100	730 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.3	0.3	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	0.56 × 0.56	0.56 × 0.56	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	2.4 ... 2.8	2.4 ... 2.8	mm
Halbwinkel Half angle	φ	± 17	± 17	Grad deg.

Kennwerte ($T_A = 25\text{ °C}$)

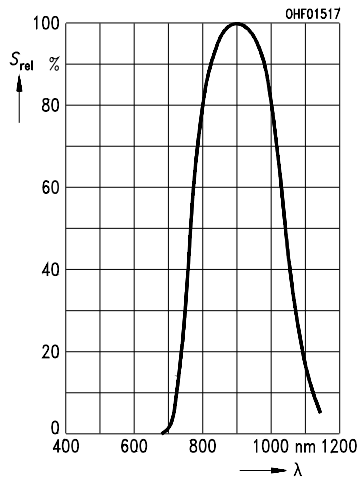
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 229	SFH 229 FA	
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	I_R	50 (≤ 5000)	50 (≤ 5000)	μA
Spektrale Fotoempfindlichkeit, $\lambda = 850\text{ nm}$ Spectral sensitivity	S_λ	0.62	0.60	A/W
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.90	0.88	<u>Electrons</u> Photon
Leerlaufspannung Open-circuit voltage $E_V = 1000\text{ lx}$, Normlicht/standard light A, $T = 2856\text{ K}$ $E_e = 0.5\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	V_O	450 (≥ 400)	–	mV
	V_O	–	420 (≥ 370)	mV
Kurzschlußstrom Short-circuit current $E_V = 1000\text{ lx}$, Normlicht/standard light A, $T = 2856\text{ K}$ $E_e = 0.5\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	I_{SC}	27	–	μA
	I_{SC}	–	9	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\ \Omega$; $V_R = 10\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\ \mu\text{A}$	t_r, t_f	10	10	ns
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	13	13	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	– 2.6	– 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC} Normlicht/standard light A $\lambda = 950\text{ nm}$	TC_I	0.18 –	– 0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$	NEP	6.5×10^{-15}	6.5×10^{-15}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	8.4×10^{12}	8.4×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

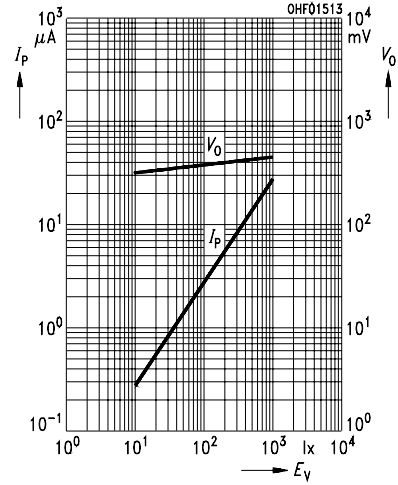
Relative Spectral Sensitivity
 $S_{rel} = f(\lambda)$
SFH 229



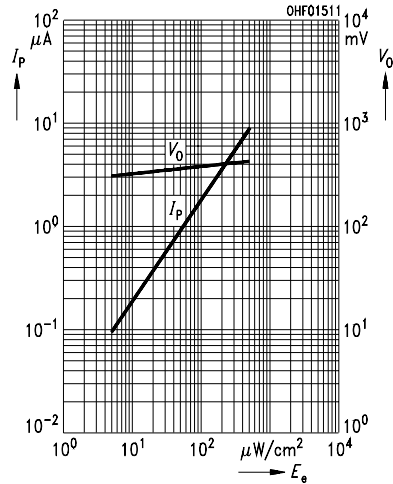
Relative Spectral Sensitivity
 $S_{rel} = f(\lambda)$
SFH 229 FA



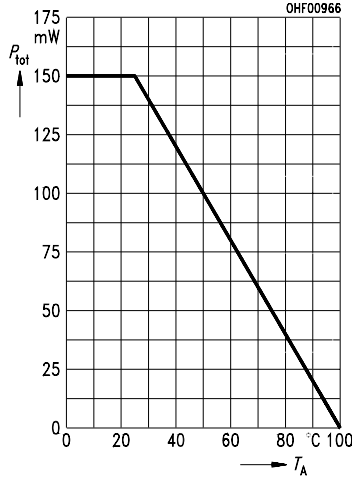
Photocurrent $I_P = f(E_v)$, $V_R = 5 V$
Open-Circuit Voltage $V_O = f(E_v)$
SFH 229



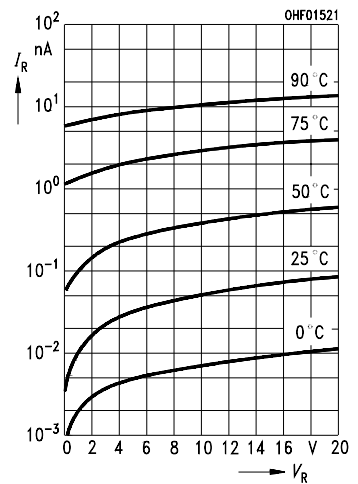
Photocurrent $I_P = f(E_e)$, $V_R = 5 V$
Open-Circuit Voltage $V_O = f(E_e)$
SFH 229 FA



Total Power Dissipation
 $P_{tot} = f(T_A)$

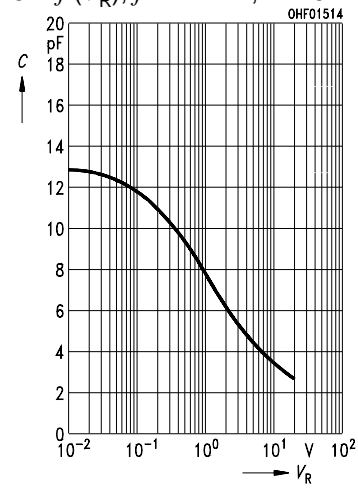


Dark Current
 $I_R = f(V_R), E = 0$



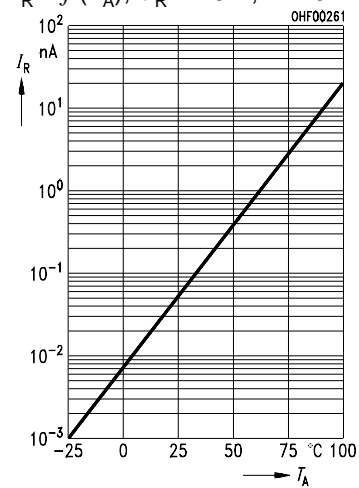
Capacitance

$C = f(V_R), f = 1 \text{ MHz}, E = 0$



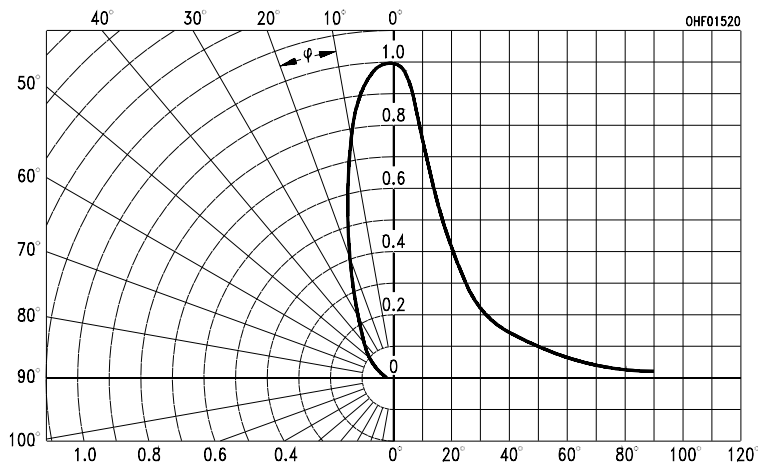
Dark Current

$I_R = f(T_A), V_R = 10 \text{ V}, E = 0$

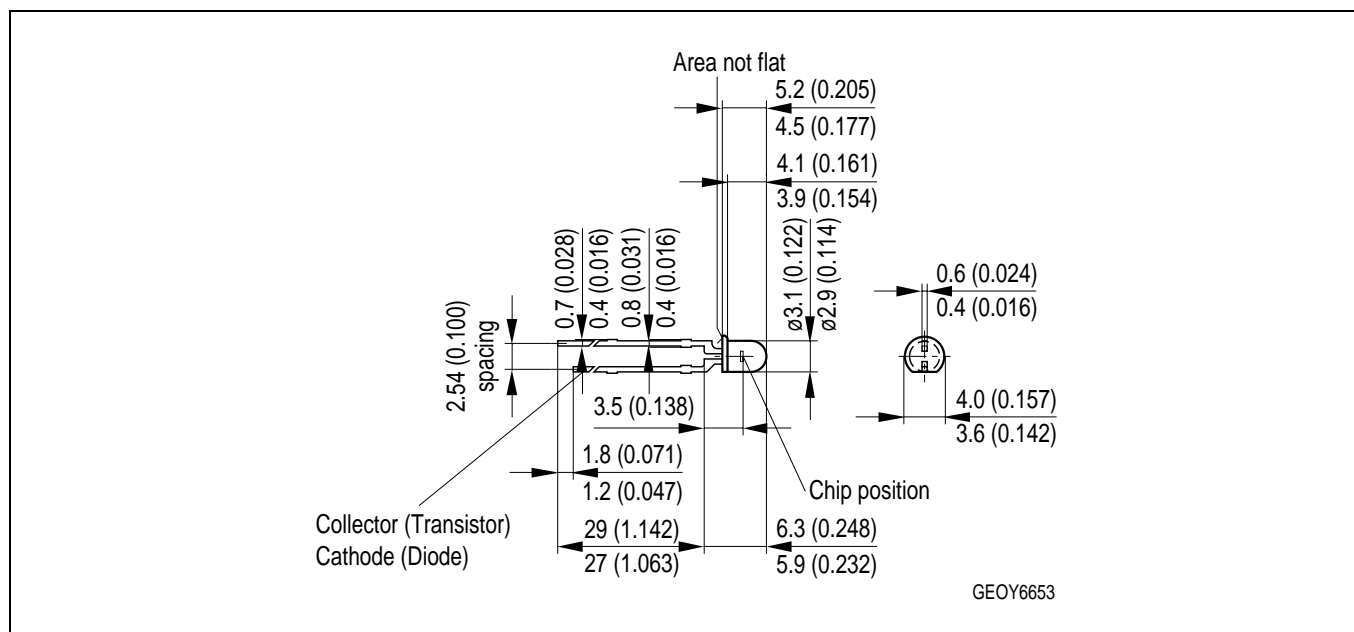


Directional Characteristics

$S_{rel} = f(\varphi)$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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